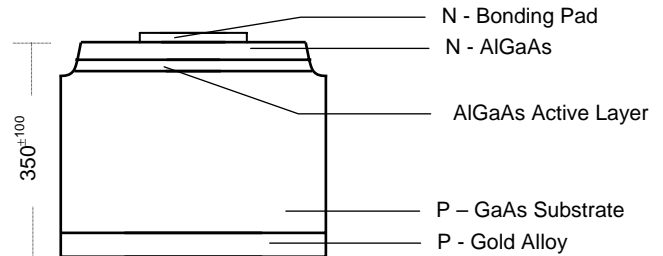
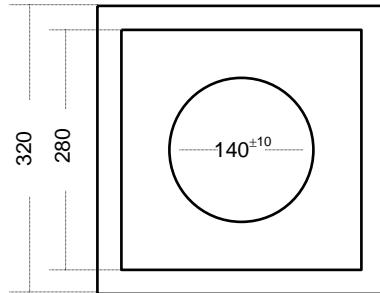


TCD770

❖ Outline Dimensions:

Unit: μm



❖ Physical Structure:

Chip dimensions	Chip size	12 mil x 12 mil	320 μm x 320 μm
	Thickness	13.7 mil	350 μm
	Bonding pad	5.5 mil	140 μm

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	1.80	2.40	V
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Peak Wavelength	λ_P	$I_F = 20\text{mA}$	-	770	-	nm
Radiant Flux	P_O	$I_F = 20\text{mA}$	1.0	-	-	mW